

### 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Surface-Mounted Device (SMD) package.

### 2. Features and benefits

- Average forward current I<sub>F(AV)</sub> ≤ 0.2 A
- Reverse voltage V<sub>R</sub> ≤ 20 V
- Low forward voltage typ. V<sub>F</sub> 245 mV
- Low forward current typ. I<sub>F</sub> 10 μA
- Ultra small and leadless SMD package
- Package height typ. 0.3 mm

# 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- LED backlight for mobile application

## 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I <sub>F(AV)</sub> average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{amb}$ = 115 °C; square wave	[1]	-	-	0.2	A	
		$\delta$ = 0.5 ; f = 20 kHz; T <sub>sp</sub> = 125 °C; square wave		-	-	0.2	A
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 mA; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta \le 0.02$ ; T <sub>j</sub> = 25 °C		-	245	310	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	5	-	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.





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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]		1 🛃 2
2	А	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

[1] The marking bar indicates the cathode.

# 6. Ordering information

Table 3.       Ordering information					
Type number Package					
	Name	Description	Version		
PMEG2002AESF	DSN0603-2	Leadless ultra small package; 2 terminals; body 0.6 x 0.3 x 0.3 mm	SOD962-2		

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG2002AESF	A

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	20	V
l <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 120 °C		-	0.28	А
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{amb}$ = 115 °C; square wave	[1]	-	0.2	A
		$\delta$ = 0.5 ; f = 20 kHz; $T_{sp}$ = 125 °C; square wave		-	0.2	A
I <sub>FRM</sub>	repetitive peak forward current	t <sub>p</sub> ≤ 1 ms; δ ≤ 0.25		-	2	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	4.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	325	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	525	mW
			[1]	-	950	mW
Tj	junction temperature			-	125	°C
T <sub>amb</sub>	ambient temperature			-55	125	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

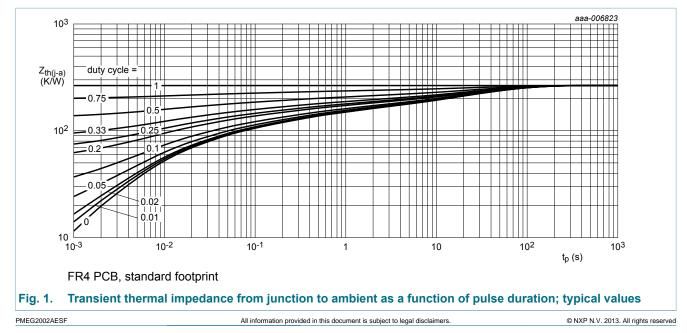
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

### 9. Thermal characteristics

Table 6.       Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	310	K/W
from junction to ambient			[1][3]	-	-	190	K/W
c	ambient		[1][4]	-	-	105	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	40	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

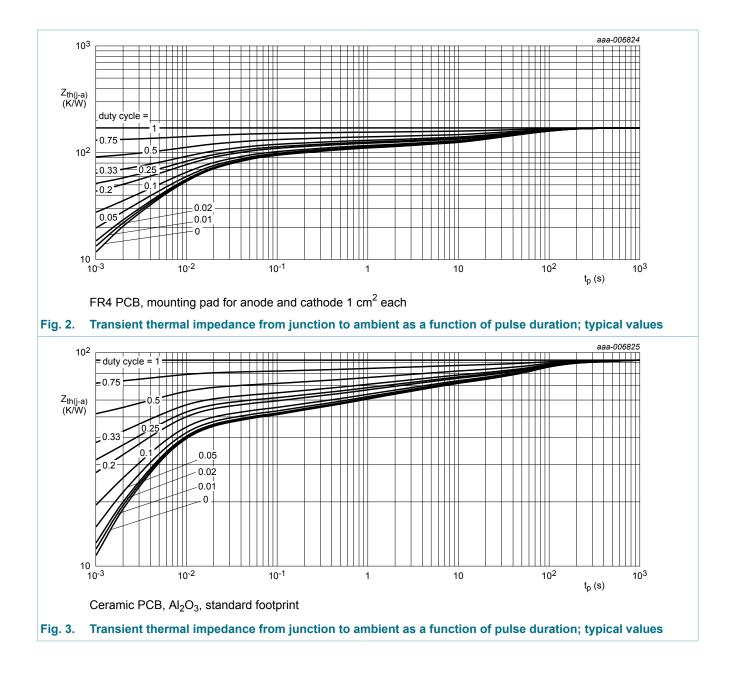
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.



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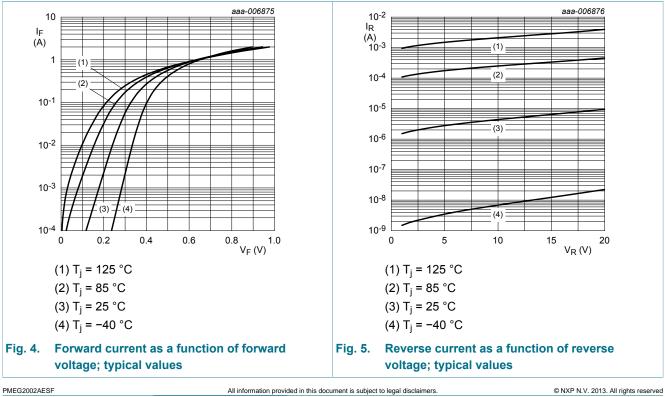
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## **10. Characteristics**

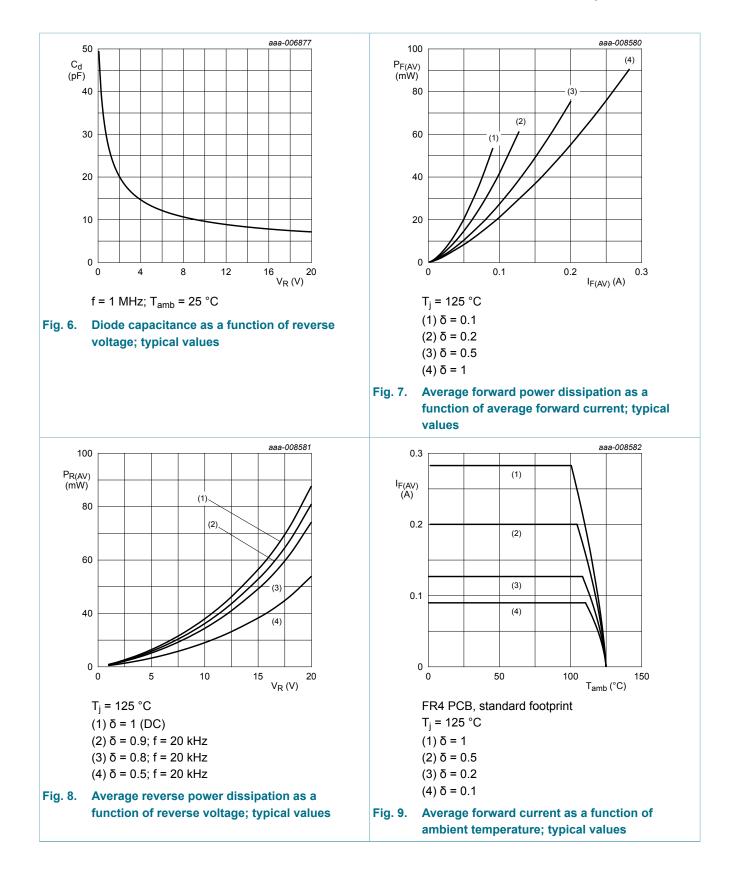
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub> forward voltage	forward voltage	I <sub>F</sub> = 0.1 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>j</sub> = 25 °C	-	120	180	mV
	$I_F$ = 1 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>j</sub> = 25 °C	-	180	250	mV	
		$I_F$ = 10 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>j</sub> = 25 °C	-	245	310	mV
	$I_F$ = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>j</sub> = 25 °C	-	330	380	mV	
	I <sub>F</sub> = 200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; $\delta \le 0.02$ ; T <sub>j</sub> = 25 °C	-	375	420	mV	
I <sub>R</sub> reverse current	reverse current	V <sub>R</sub> = 6 V; T <sub>j</sub> = 25 °C	-	3.2	20	μA
		V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	5	-	μA
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 25 °C	-	10	45	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	25	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	10	-	pF
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 200 mA; I <sub>R</sub> = 200 mA; I <sub>R(meas)</sub> = 40 mA; T <sub>i</sub> = 25 °C	-	1.9	-	ns



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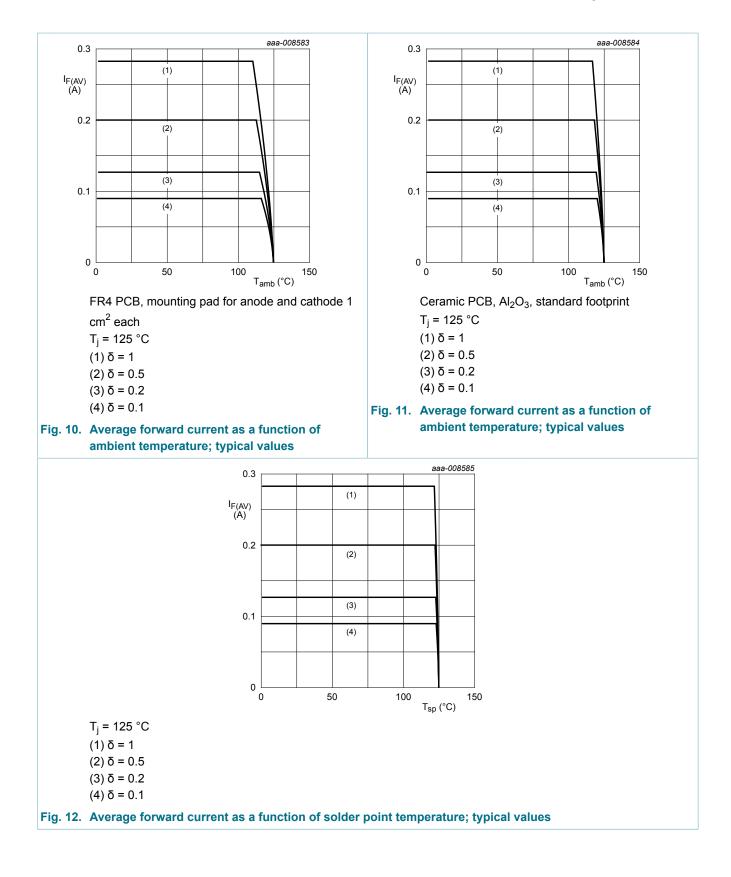
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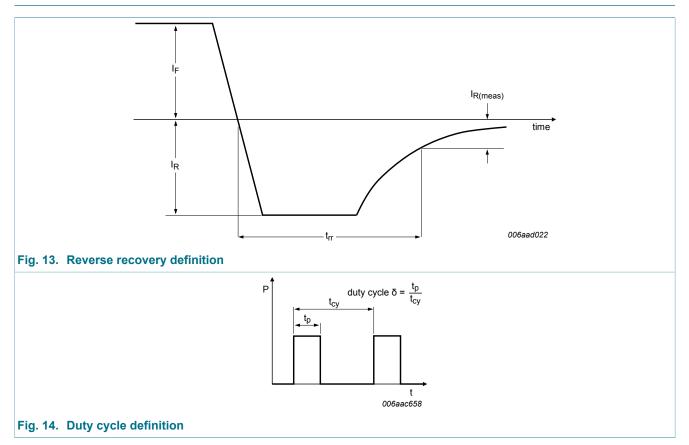


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## 11. Test information

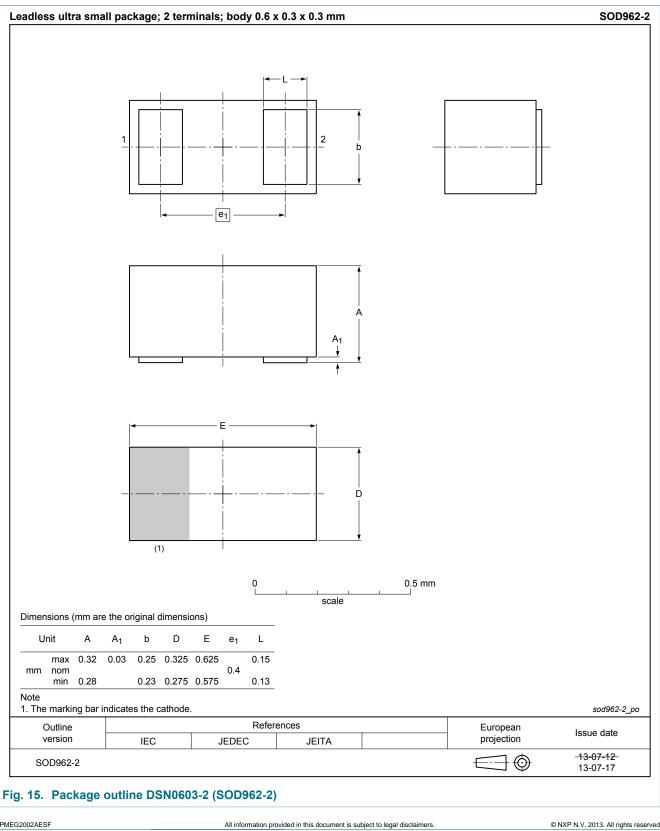


The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

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### 12. Package outline



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## 13. Soldering

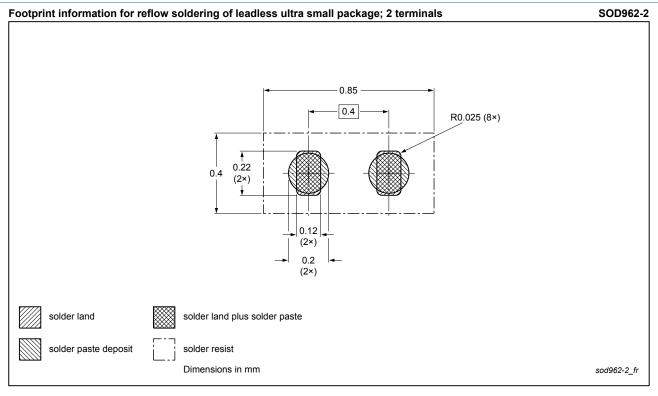


Fig. 16. Reflow soldering footprint for DSN0603-2 (SOD962-2)

## 14. Revision history

Table 8.   Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMEG2002AESF v.2	20131008	Product data sheet	-	PMEG2002AESF v.1	
Modifications:	Product status char	nged			
PMEG2002AESF v.1	20130301	Objective data sheet	-	-	

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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